

# **METHOD OF MANUFACTURING FLASH MEMORY DEVICE**

## **ABSTRACT OF THE DISCLOSURE**

5           The present invention relates a method of manufacturing a flash  
memory device. In case of forming a dielectric film consisting of a lower  
oxide film, a nitride film and upper oxide film that is formed between a  
floating gate and a control gate, a nitrification process is performed after the  
lower oxide film is formed, thus forming a nitrogen layer below the lower  
10 oxide film. Then, an annealing process using an oxygen gas is performed to  
move the nitrogen layer onto the surface of the lower oxide film, thus forming  
a nitride film. Therefore, the present invention can reduce the effective  
thickness of the dielectric film.